

TEM studies of nanocrystal formation in PECVD grown for SiO₂:Ge/SiO₂ multilayers

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Corrigendum

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In figure 4(c) the diffraction pattern of the Si substrate was inadvertently included instead of the diffraction pattern of Ge nanocrystals, as shown below:

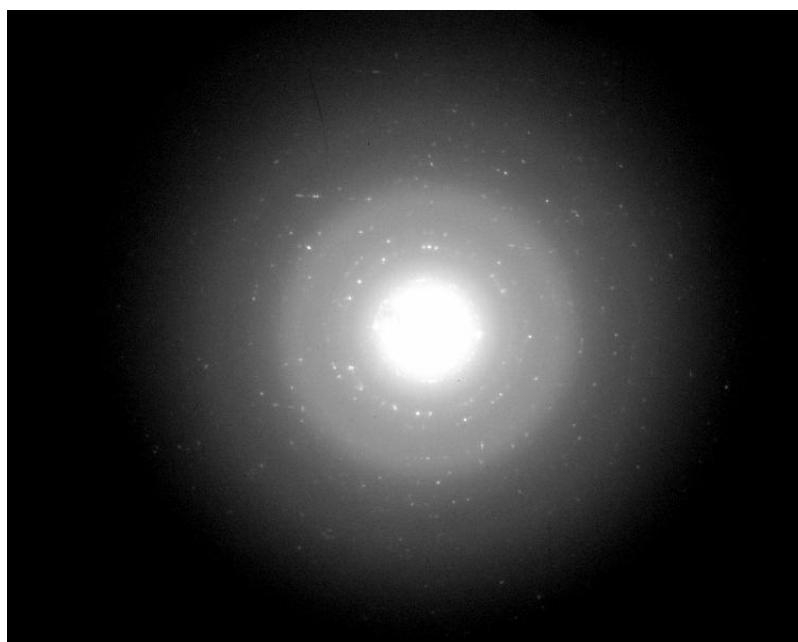


Figure 4(c). Electron beam diffraction pattern of Ge nanocrystals